

OCT. 5. 2004 4:13PM

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NO. 1081—P. 4

Substitute for form 1449A/PTO				<i>Complete if Known</i>	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	10/642,305
				Filing Date	August 18, 2003
				Firm Named Inventor	Hongyong ZHANG et al.
				Art Unit	2811
				Examiner Name	D. Owens
Sheet	1	of	7	Attorney Docket Number	740756-2646

U.S. PATENT DOCUMENTS					
Examiner Initials ¹	Cite No. ²	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Col. & Lines, Where Relevant In Pages & Relevant Filings Appear
		Number - Kind Code ³ (if known)			
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		US-5,105,245	04/14/1992	Riemenschneider et al.	
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Examiner Signature	Date Considered
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PAGE 4/10 * RCVD AT 10/5/2004 4:08:41 PM [Eastern Daylight Time] * SVR:USPTO-EFXRF-1/0 * DNIS:8729306 * CSID:703 880 0669 * DURATION (mm:ss):02:54

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NO. 1081 P. 6

Substitute for Form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				<i>Complete if Known</i>	
Sheet	3	of	7	Application Number	10/642,305
				Filing Date	August 18, 2003
				First Named Inventor	Hongyong ZHANG et al.
				Art Unit	2811
				Examiner Name	D. Owens
				Attorney Docket Number	740756-2646
FOREIGN PATENT DOCUMENTS					
Examiner Unit(s)	Cite No. ¹	Foreign Patent Document		Name of Patentee or Application of Cited Document	Pages, Columna, Linea, Where Relevant Passages or Relevant Figures Appear
		Country Code ² Number ³	Kind Code ⁴ (if known)		
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				<i>Complete if Known</i>	
Sheet	4	of	7	Application Number	10/642,305
				Filing Date	August 18, 2003
				First Named Inventor	Hongyong ZHANG et al.
				Art Unit	2811
				Examiner Name	D. Owens
				Attorney Docket Number	740756-2646

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS		
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
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		S. Suyama et al., IEEE Trans. Electron Dev., 34(10) (1987) 2124, "...MOSFET's Utilizing Oxygen-Argon Sputter-Deposited Gate Oxide Films", October, 1987.
		T.I. Kamins et al., IEEE Electron Dev. Lett. Vol EDL-1, No. 8, 159 "Hydrogenation of transistors fabricated in Polycrystalline-Silicon Films", August, 1980.
		Katoda, "Estimation of a Semiconductor by a Laser Raman Spectroscopy", Published by Tokyo University, 1988, pp. 67-75 (in Japanese with Concise English Statement).
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				Filing Date	August 18, 2003
				First Named Inventor	Hongyong ZHANG et al.
				Art Unit	2811
				Examiner Name	D. Owens
				Attorney Docket Number	740756-2646
Sheet	5	of	7		

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NO. 1081 P. 9

Form PTO-1449 (Rev. 8-83)		U.S. Department of Com Patent and Trademark		Attorney Docket: 740756-2646		Serial No. 10/642,305	
INFORMATION DISCLOSURE STATEMENT						Sheet 6 of 7	
(Use several sheets if necessary)							
				Applicant: Hongyong ZHANG et al.			
				Filing Date: August 18, 2003		Grp: 2811	
U.S. PATENT DOCUMENTS							
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)	
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	G. Kawachi et al., "Large-Area Doping Process for Fabrication of poly-Si Thin Film Transistors Using Bucket Ion Source and XeCl Excimer Laser Annealing", Japanese Journal of Applied Physics, Vol. 29, No. 12, December 1990, pp. L2370-L2372						
Examiner	Date Considered						

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Sheet 7 of 7

Form PTO-1449 (Rev. 8-83)		U.S. Department of Commerce Patent and Trademark Office	Attorney Docket: 740756- 2646	Serial No. 10/642,305		
INFORMATION DISCLOSURE STATEMENT						
(Use several sheets if necessary)		Applicant: Hongyong ZHANG et al. Filing Date: August 18, 2003 Group: 2811				
FOREIGN PATENT DOCUMENTS						
	Document Number	Date	Country	Class	Subclass	Translation Yes No
	57-109377	07/07/82	Japan			Abstract
	58-002073	01/07/83	Japan			Full
	58-182816	10/25/83	Japan			Abstract
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